

# MOS FIELD EFFECT TRANSISTOR

# 2SK3294

## SWITCHING

## N-CHANNEL POWER MOS FET

### DESCRIPTION

The 2SK3294 is N-channel MOS FET device that features a low on-state resistance and excellent switching characteristics, and designed for high voltage applications such as DC/DC converter, actuator driver.

### FEATURES

- Gate voltage rating  $\pm 30$  V
- Low on-state resistance  
 $R_{DS(on)} = 160 \text{ m}\Omega \text{ MAX. (} V_{GS} = 10 \text{ V, } I_D = 10 \text{ A)}$
- Low input capacitance  
 $C_{iss} = 1500 \text{ pF TYP. (} V_{DS} = 10 \text{ V, } V_{GS} = 0 \text{ V)}$
- Avalanche capability rated
- Built-in gate protection diode
- Surface mount device available

### ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^\circ\text{C}$ )

Drain to Source Voltage ( $V_{GS} = 0 \text{ V}$ )	$V_{DSS}$	250	V
Gate to Source Voltage ( $V_{DS} = 0 \text{ V}$ )	$V_{GSS}$	$\pm 30$	V
Drain Current (DC) ( $T_C = 25^\circ\text{C}$ )	$I_{D(DC)}$	$\pm 20$	A
Drain Current (Pulse) <sup>Note1</sup>	$I_{D(pulse)}$	$\pm 60$	A
Total Power Dissipation ( $T_C = 25^\circ\text{C}$ )	$P_{T1}$	100	W
Total Power Dissipation ( $T_A = 25^\circ\text{C}$ )	$P_{T2}$	1.5	W
Channel Temperature	$T_{ch}$	150	$^\circ\text{C}$
Storage Temperature	$T_{stg}$	$-55 \text{ to } +150$	$^\circ\text{C}$
Single Avalanche Current <sup>Note2</sup>	$I_{AS}$	20	A
Single Avalanche Energy <sup>Note2</sup>	$E_{AS}$	150	mJ

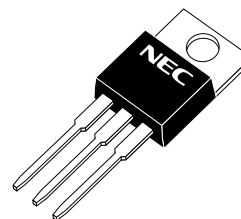
**Notes** 1.  $PW \leq 10 \mu\text{s}$ , Duty Cycle  $\leq 1\%$

2. Starting  $T_{ch} = 25^\circ\text{C}$ ,  $V_{DD} = 150 \text{ V}$ ,  $R_G = 25 \Omega$ ,  $V_{GS} = 20 \text{ V} \rightarrow 0 \text{ V}$

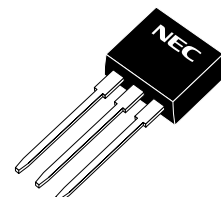
### ORDERING INFORMATION

PART NUMBER	PACKAGE
2SK3294	TO-220AB
2SK3294-S	TO-262
2SK3294-ZJ	TO-263(MP-25ZJ)

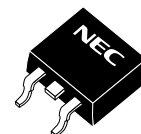
(TO-220AB)



(TO-262)



(TO-263)

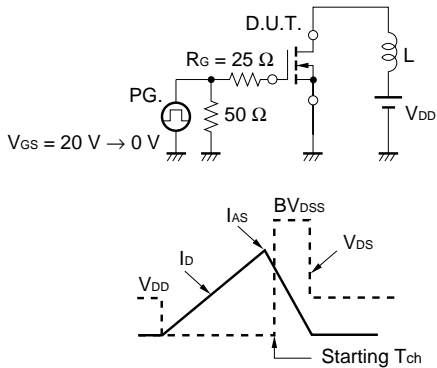


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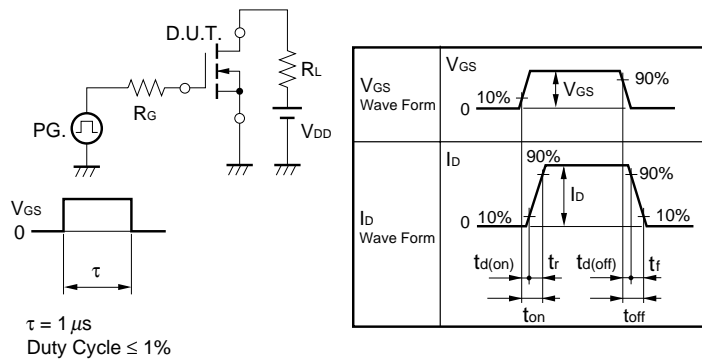
**ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25°C)**

Characteristics	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 250 V, V <sub>GS</sub> = 0 V			100	μA
Gate Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = ±30 V, V <sub>DS</sub> = 0 V			±10	μA
Gate Cut-off Voltage	V <sub>GS(off)</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 1 mA	2.5		4.5	V
Forward Transfer Admittance	y <sub>fs</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 10 A	6.0			S
Drain to Source On-state Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 10 A		120	160	mΩ
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 10 V		1500		pF
Output Capacitance	C <sub>oss</sub>	V <sub>GS</sub> = 0 V		360		pF
Reverse Transfer Capacitance	C <sub>rss</sub>	f = 1 MHz		220		pF
Turn-on Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> = 125 V, I <sub>D</sub> = 10 A		24		ns
Rise Time	t <sub>r</sub>	V <sub>GS</sub> = 10 V		78		ns
Turn-off Delay Time	t <sub>d(off)</sub>	R <sub>G</sub> = 10 Ω		110		ns
Fall Time	t <sub>f</sub>			60		ns
Total Gate Charge	Q <sub>G</sub>	V <sub>DD</sub> = 200 V		57		nC
Gate to Source Charge	Q <sub>GS</sub>	V <sub>GS</sub> = 10 V		8		nC
Gate to Drain Charge	Q <sub>GD</sub>	I <sub>D</sub> = 20 A		36		nC
Body Diode Forward Voltage	V <sub>F(S-D)</sub>	I <sub>F</sub> = 20 A, V <sub>GS</sub> = 0 V		1.0		V
Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 20 A, V <sub>GS</sub> = 0 V		340		ns
Reverse Recovery Charge	Q <sub>rr</sub>	di/dt = 50 A/μs		2.1		μC

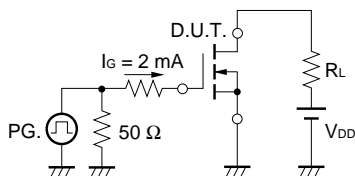
**TEST CIRCUIT 1 AVALANCHE CAPABILITY**



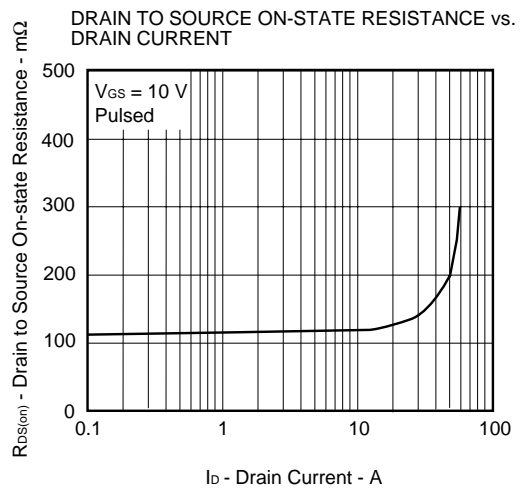
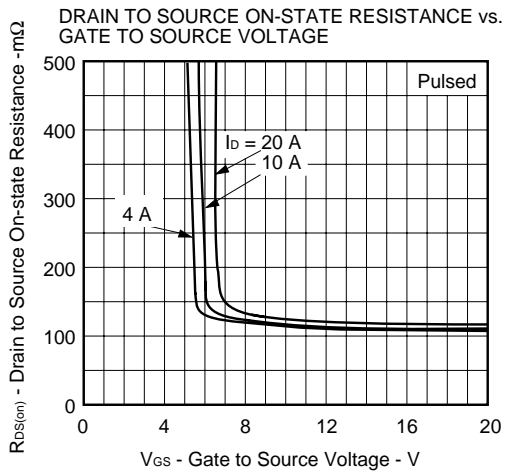
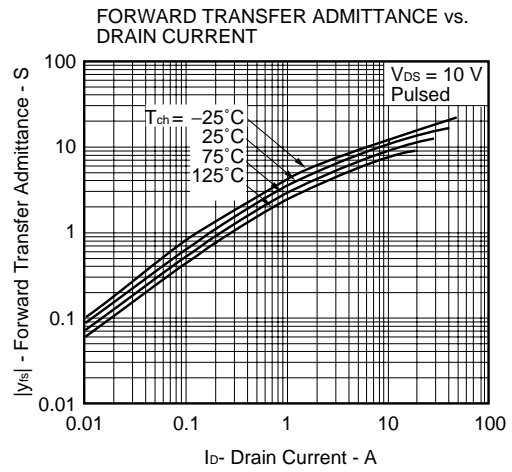
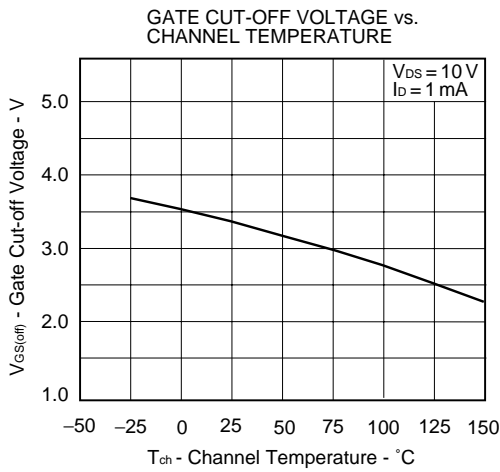
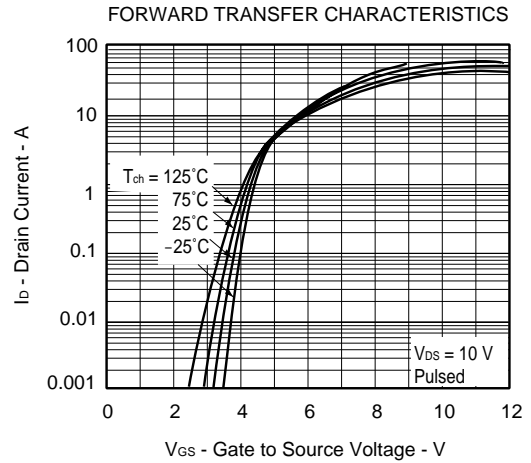
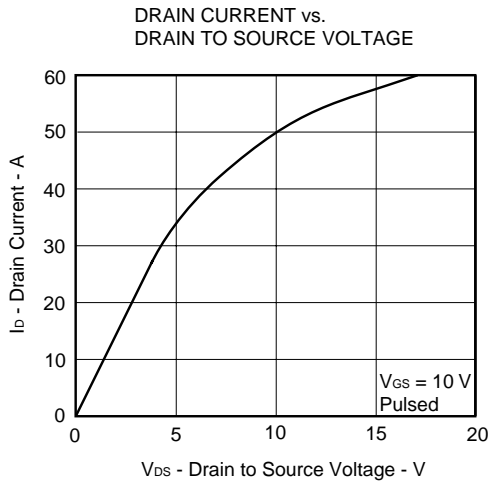
**TEST CIRCUIT 2 SWITCHING TIME**

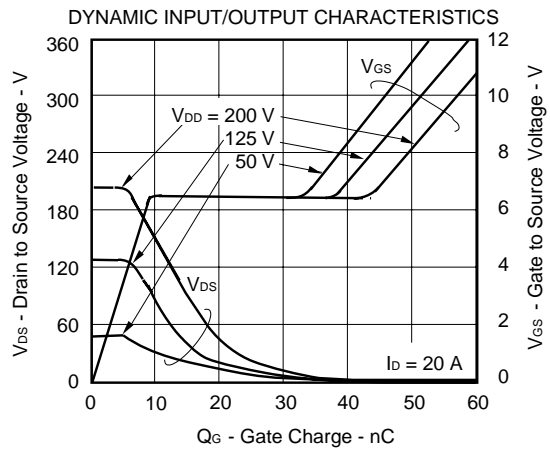
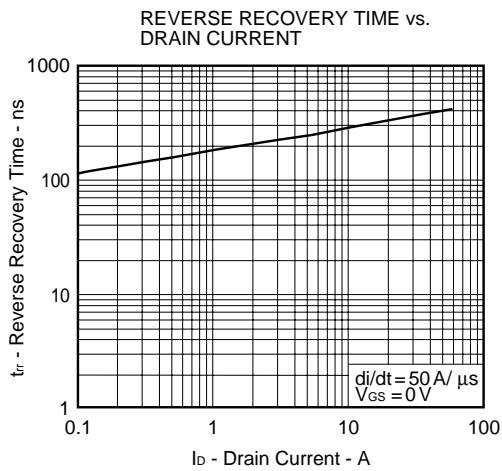
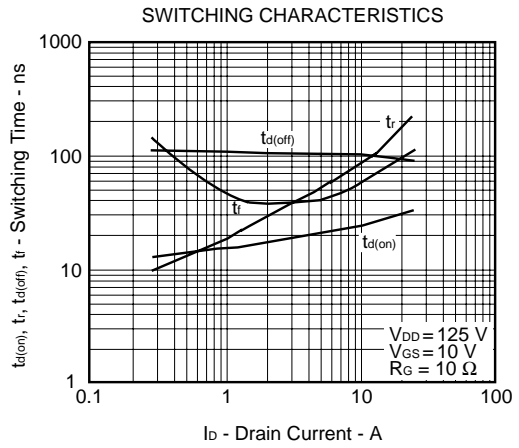
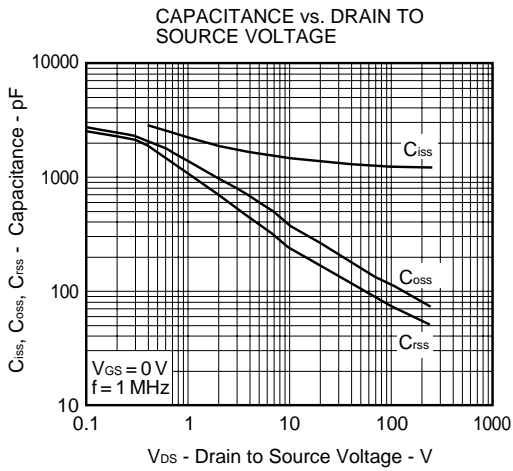
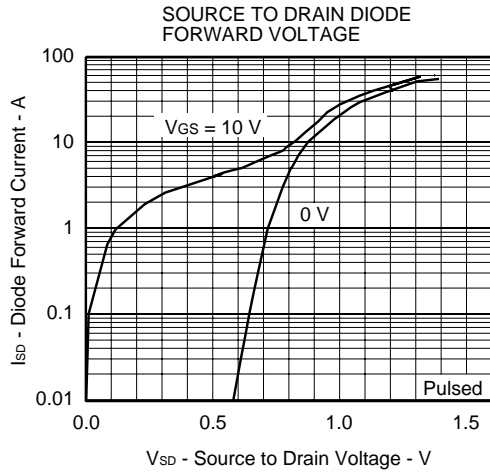
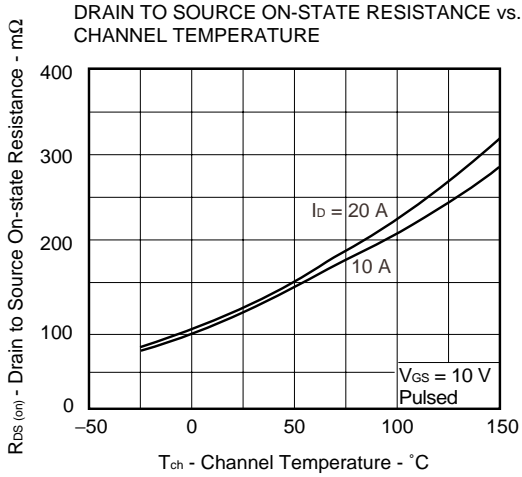


**TEST CIRCUIT 3 GATE CHARGE**

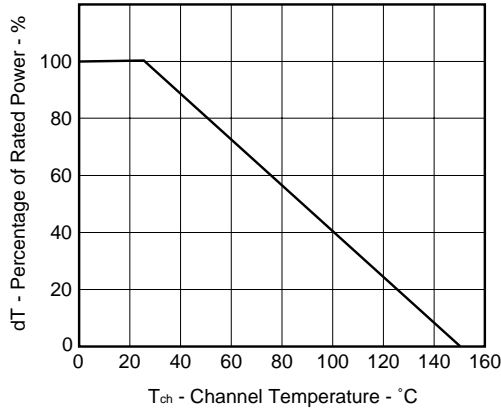


TYPICAL CHARACTERISTICS (T<sub>A</sub> = 25°C)

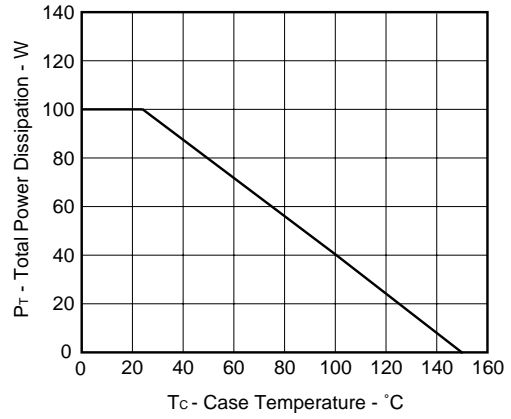




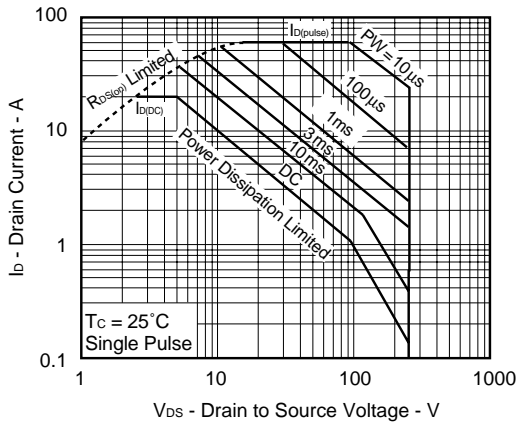
DERATING FACTOR OF FORWARD BIAS SAFE OPERATING AREA



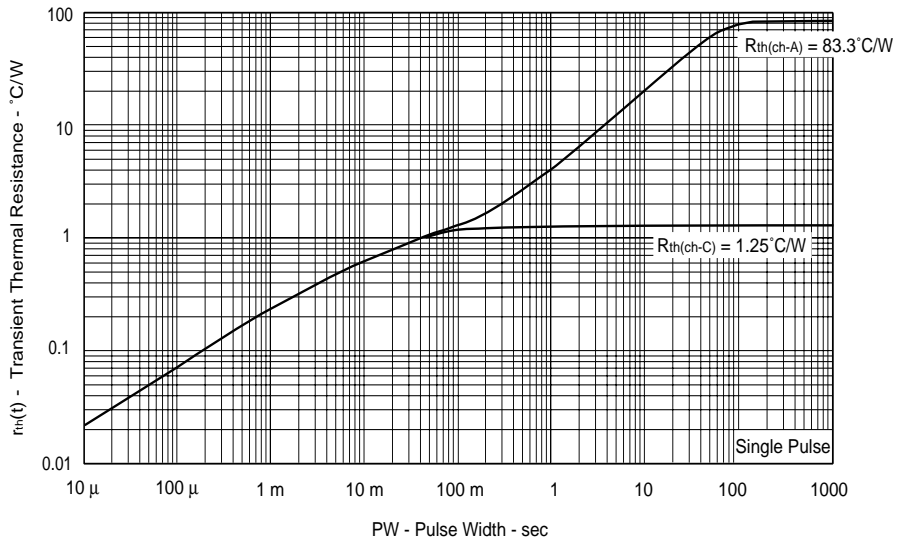
TOTAL POWER DISSIPATION vs. CASE TEMPERATURE

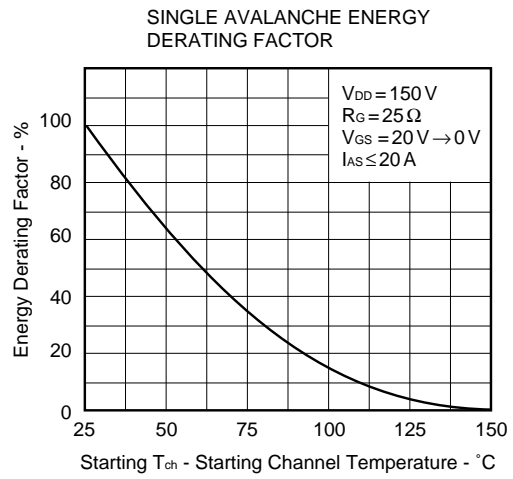
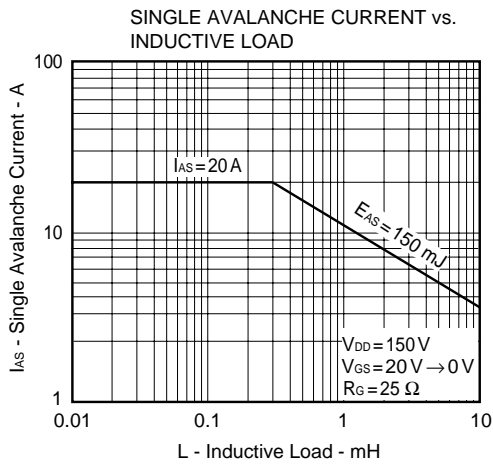


FORWARD BIAS SAFE OPERATING AREA



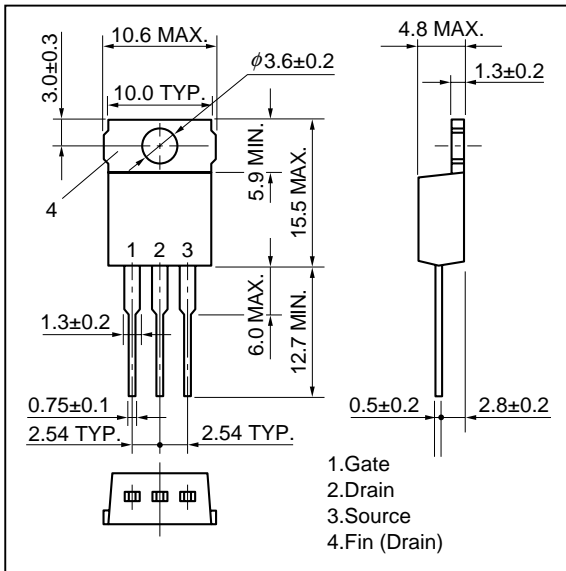
TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH



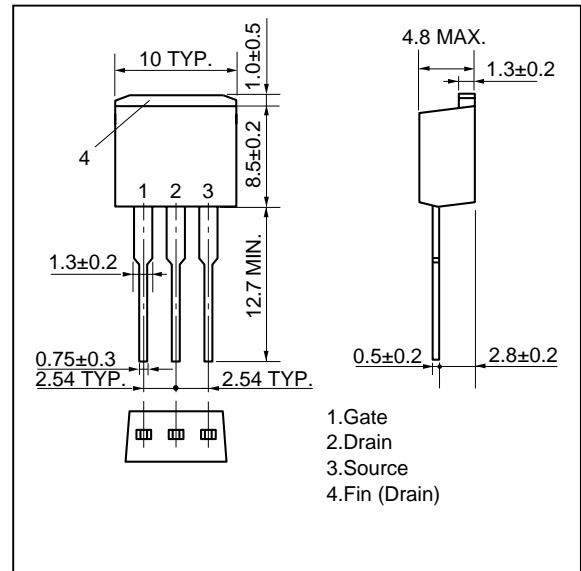


PACKAGE DRAWINGS (Unit: mm)

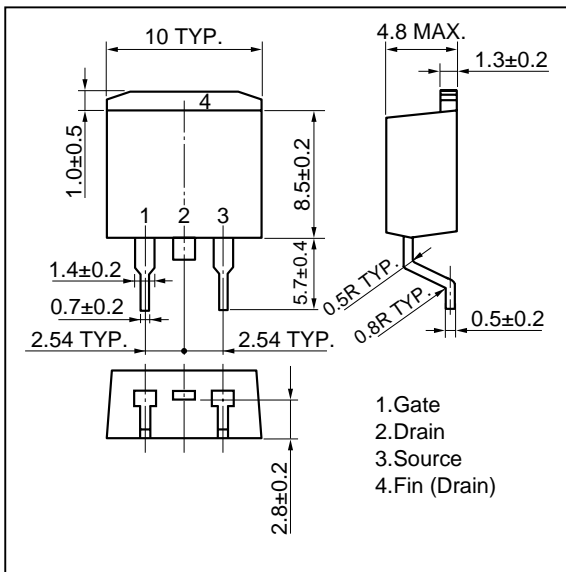
1) TO-220AB (MP-25)



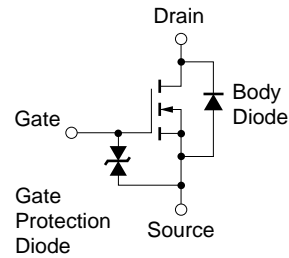
2) TO-262



3) TO-263 (MP-25ZJ)



EQUIVALENT CIRCUIT



**Remark** The diode connected between the gate and source of the transistor serves as a protector against ESD. When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.

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